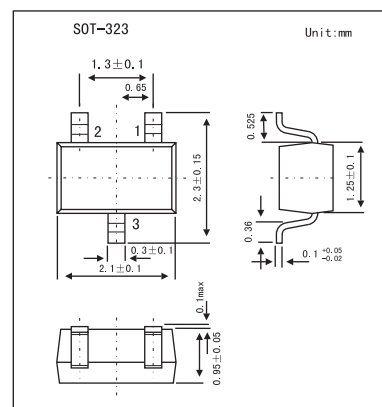


Schottky barrier(double) diodes

BAS70W;BAS70-04W
BAS70-05W;BAS70-06W

■ Features

- Low forward voltage
- High breakdown voltage
- Guard ring protected
- Very small SMD package
- Low capacitance.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			70	V
Continuous forward current	I_F			70	mA
Repetitive peak forward current	I_{FRM}	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		70	mA
Non-repetitive peak forward current	I_{FSM}	$t_p < 10 \text{ ms}$		100	mA
Storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
Junction temperature	T_j			150	$^\circ\text{C}$
Operating ambient temperature	T_{amb}		-65	+150	$^\circ\text{C}$
Thermal resistance from junction to ambient	$R_{th j-a}$	Note 1		625	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Condition	Max	Unit
Forward Voltage	V_F	$I_F = 1 \text{ mA}$	410	mV
		$I_F = 10 \text{ mA}$	750	mV
		$I_F = 15 \text{ mA}$	1	V
Reverse Current	I_R	$V_R = 50 \text{ V}; \text{note 1}$	100	nA
		$V_R = 70 \text{ V}; \text{note 1}$	10	μA
Charge carrier life time (Krakauer method)	τ	$I_F = 5 \text{ mA}$	100	ps
Diode capacitance	C_d	$f = 1 \text{ MHz}; V_R = 0$	2	pF

Note

1. Pulse test: $t_p = 300 \text{ ms}; d = 0.02$.

■ Marking

Type	BAS70W	BAS70-04W	BAS70-05W	BAS70-06W
Marking	73*	74*	75*	76*